

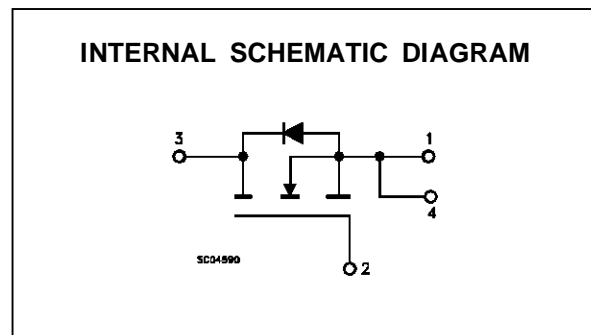
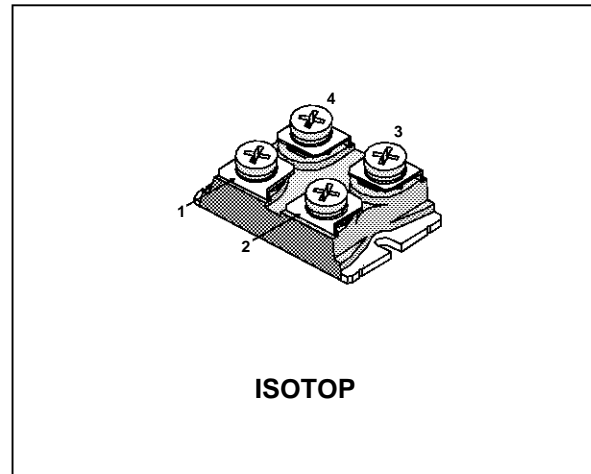
N - CHANNEL ENHANCEMENT MODE POWER MOS TRANSISTOR IN ISOTOP PACKAGE

TYPE	V _{DSS}	R _{DS(on)}	I _D
STE22N80	800 V	< 0.4 Ω	22 A

- HIGH CURRENT POWER MODULE
- AVALANCHE RUGGED TECHNOLOGY (SEE STH8N80 FOR RATING)
- VERY LARGE SOA - LARGE PEAK POWER CAPABILITY
- EASY TO MOUNT
- SAME CURRENT CAPABILITY FOR THE TWO SOURCE TERMINALS
- EXTREMELY LOW R_{th} JUNCTION TO CASE
- VERY LOW DRAIN TO CASE CAPACITANCE
- VERY LOW INTERNAL PARASITIC INDUCTANCE (TYPICALLY < 5 nH)
- ISOLATED PACKAGE UL RECOGNIZED (FILE No E81743)

INDUSTRIAL APPLICATIONS:

- SMPS & UPS
- MOTOR CONTROL
- WELDING EQUIPMENT
- OUTPUT STAGE FOR PWM, ULTRASONIC CIRCUITS



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-Source Voltage (V _{GS} = 0)	800	V
V _{DGR}	Drain-Gate Voltage (R _{GS} = 20 kΩ)	800	V
V _{GS}	Gate-Source Voltage	± 20	V
I _D	Drain Current (continuous) at T _c = 25 °C	22	A
I _D	Drain Current (continuous) at T _c = 100 °C	13.5	A
I _{DM} (●)	Drain Current (pulsed)	88	A
P _{tot}	Total Dissipation at T _c = 25 °C	400	W
	Derating Factor	3.2	W/°C
T _{stg}	Storage Temperature	-55 to 150	°C
T _j	Max. Operating Junction Temperature	150	°C
V _{ISO}	Insulation Withstand Voltage (AC-RMS)	2500	V

(●) Pulse width limited by safe operating area

STE22N80

THERMAL DATA

$R_{thj-case}$	Thermal Resistance Junction-case	Max	0.31	°C/W
R_{thc-h}	Thermal Resistance Case-heatsink With Conductive Grease Applied	Max	0.05	°C/W

ELECTRICAL CHARACTERISTICS ($T_{case} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	$I_D = 1\text{ mA}$ $V_{GS} = 0\text{ V}$	800			V
I_{DSS}	Zero Gate Voltage Drain Current ($V_{GS} = 0$)	$V_{DS} = \text{Max Rating}$ $V_{DS} = \text{Max Rating} \times 0.8$ $T_c = 125\text{ }^{\circ}\text{C}$			300 1.5	μA mA
I_{GSS}	Gate-body Leakage Current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{ V}$			± 300	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ $I_D = 1\text{ mA}$	2		4	V
$R_{DS(on)}$	Static Drain-source On Resistance	$V_{GS} = 10\text{ V}$ $I_D = 12\text{ A}$			0.4	Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$g_{fs} (*)$	Forward Transconductance	$V_{DS} = 15\text{ V}$ $I_D = 12\text{ A}$	9			S
C_{iss} C_{oss} C_{riss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	$V_{DS} = 25\text{ V}$ $f = 1\text{ MHz}$ $V_{GS} = 0\text{ V}$			8.1 1100 500	nF pF pF

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Time Rise Time	$V_{DD} = 400\text{ V}$ $I_D = 12\text{ A}$ $R_G = 4.7\text{ }\Omega$ $V_{GS} = 10\text{ V}$ (see test circuit, figure 1)		75 88	100 115	ns ns
$(di/dt)_{on}$	Turn-on Current Slope	$V_{DD} = 640\text{ V}$ $I_D = 22\text{ A}$ $R_G = 4.7\text{ }\Omega$ $V_{GS} = 10\text{ V}$ (see test circuit, figure 3)		660		A/ μs
Q_g	Total Gate Charge	$V_{DD} = 640\text{ V}$ $I_D = 22\text{ A}$ $V_{GS} = 10\text{ V}$		400		nC

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$	Off-voltage Rise Time	$V_{DD} = 640\text{ V}$ $I_D = 22\text{ A}$		62	85	ns
t_f	Fall Time	$R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$		23	33	ns
t_c	Cross-over Time	(see test circuit, figure 3)		95	125	ns

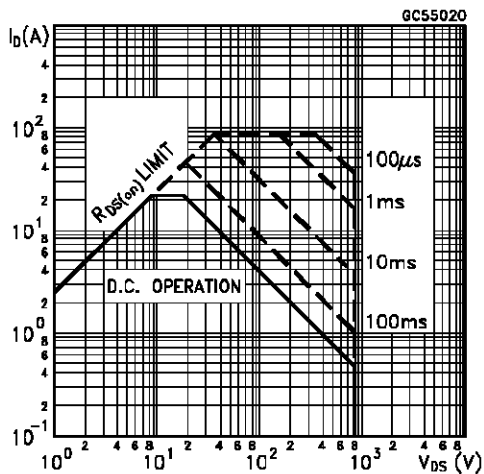
SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				22	A
$I_{SDM}(\bullet)$	Source-drain Current (pulsed)				88	A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 22\text{ A}$ $V_{GS} = 0$			2.5	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 22\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$ $T_j = 150\text{ }^\circ\text{C}$ (see test circuit, figure 3)		1400		ns
Q_{rr}	Reverse Recovery Charge			60		μC
I_{RRM}	Reverse Recovery Current			85		A

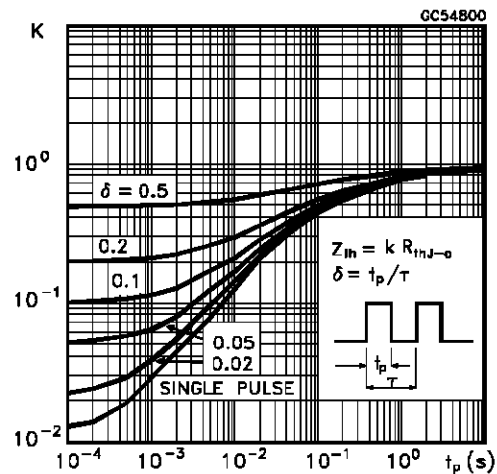
(*) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

(\bullet) Pulse width limited by safe operating area

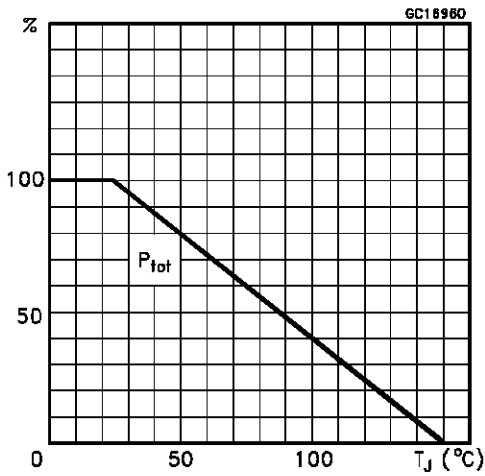
Safe Operating Area



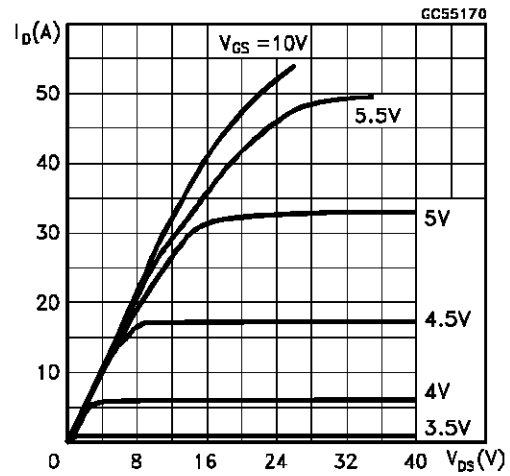
Thermal Impedance



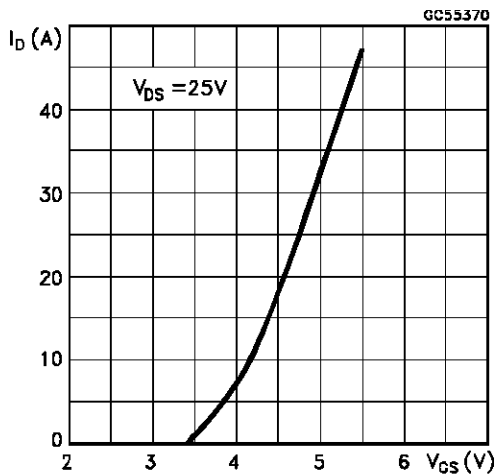
Derating Curve



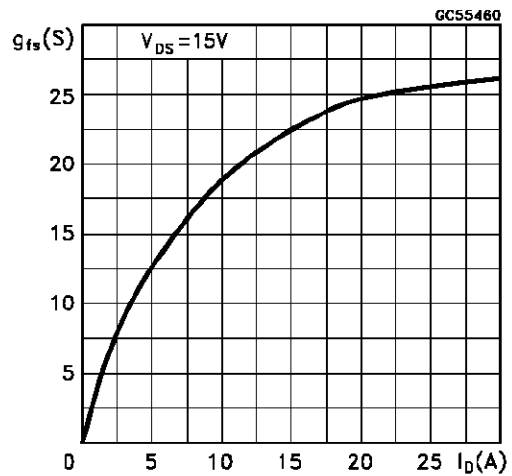
Output Characteristics



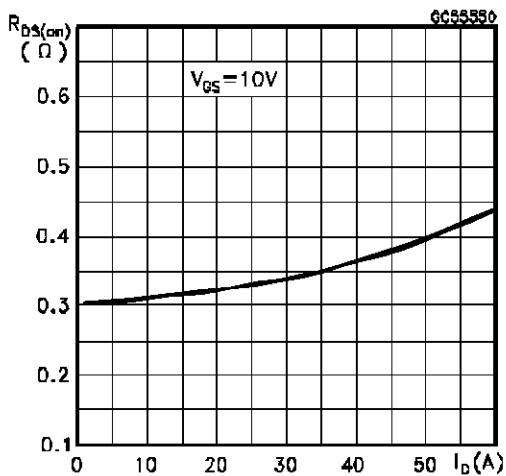
Transfer Characteristics



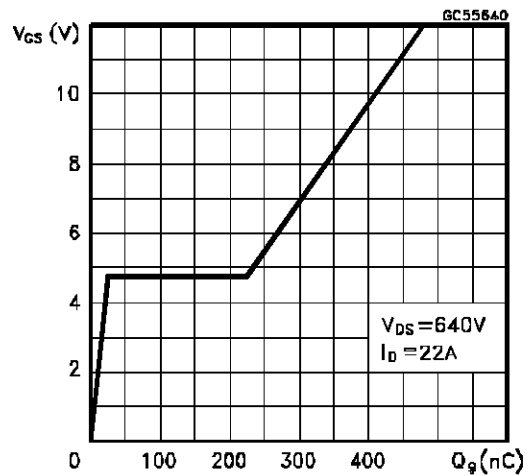
Transconductance



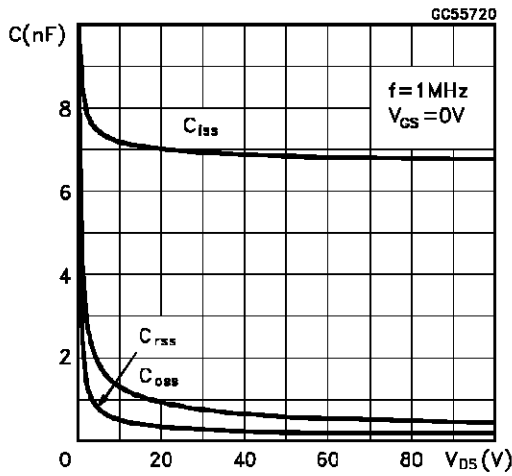
Static Drain-source On Resistance



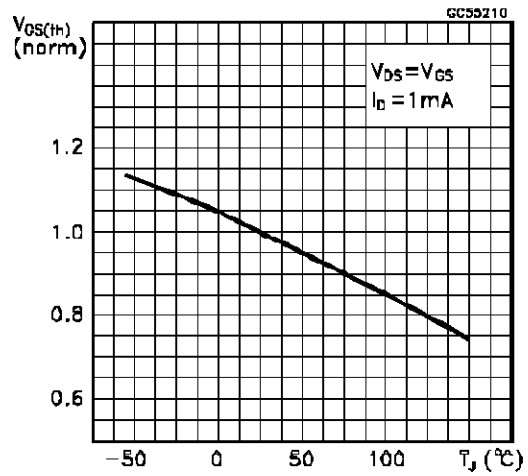
Gate Charge vs Gate-source Voltage



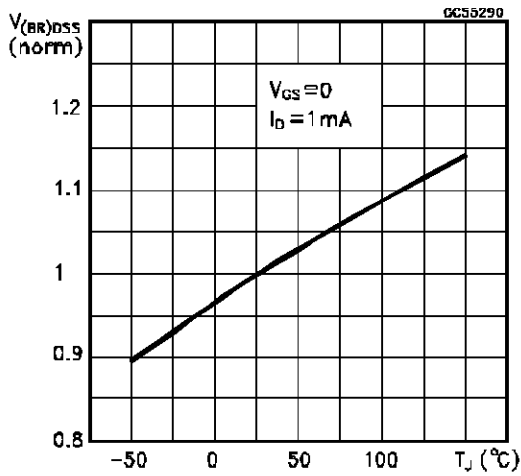
Capacitance Variations



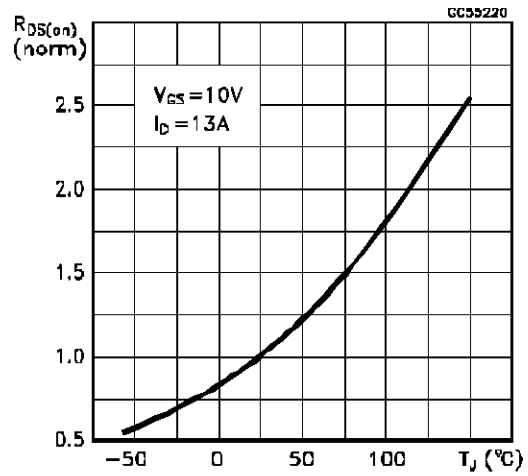
Normalized Gate Threshold Voltage vs Temperature



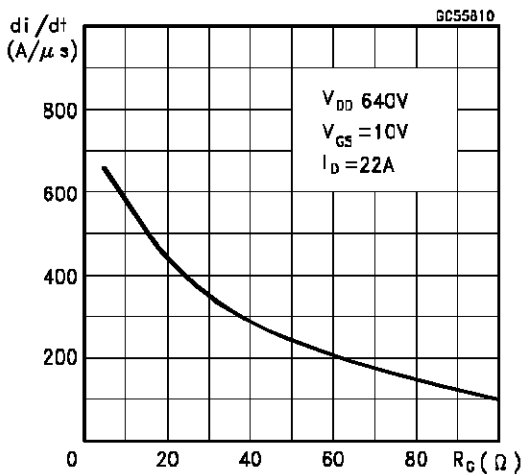
Normalized Breakdown Voltage vs Temperature



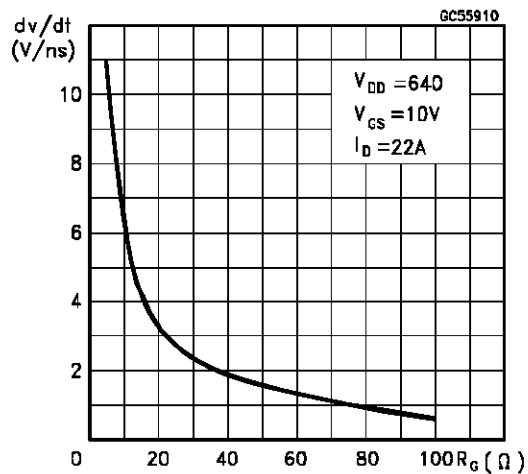
Normalized On Resistance vs Temperature



Turn-on Current Slope



Turn-off Drain-source Voltage Slope



Cross-over Time

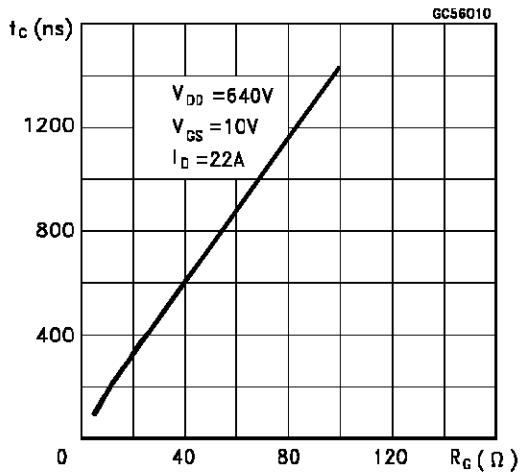
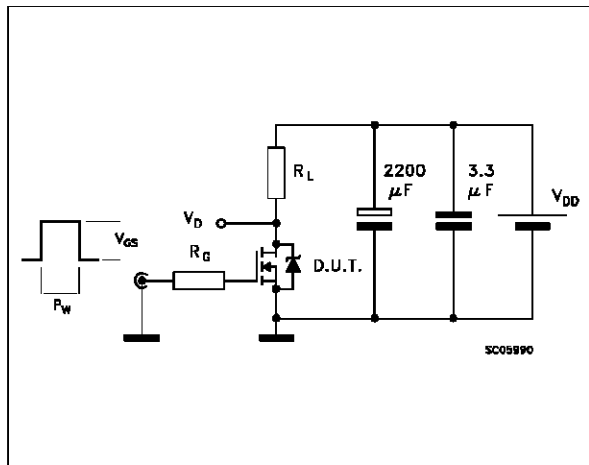


Fig. 1: Switching Times Test Circuits For Resistive Load



Source-drain Diode Forward Characteristics

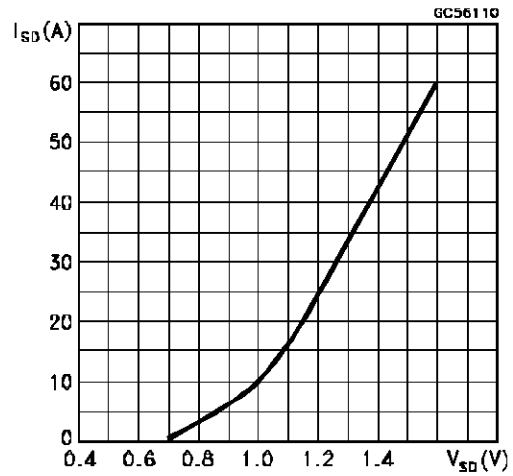


Fig. 2: Gate Charge Test Circuit

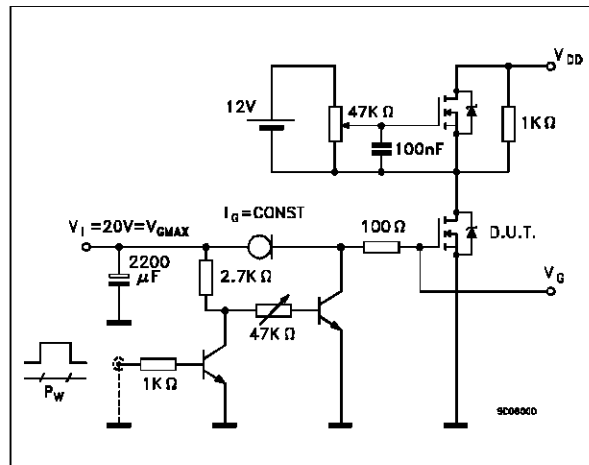
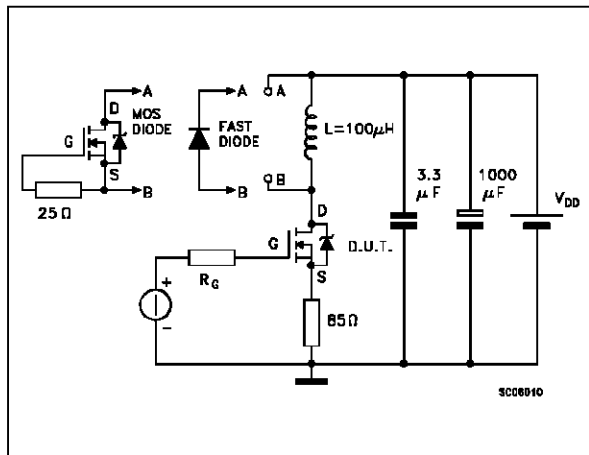
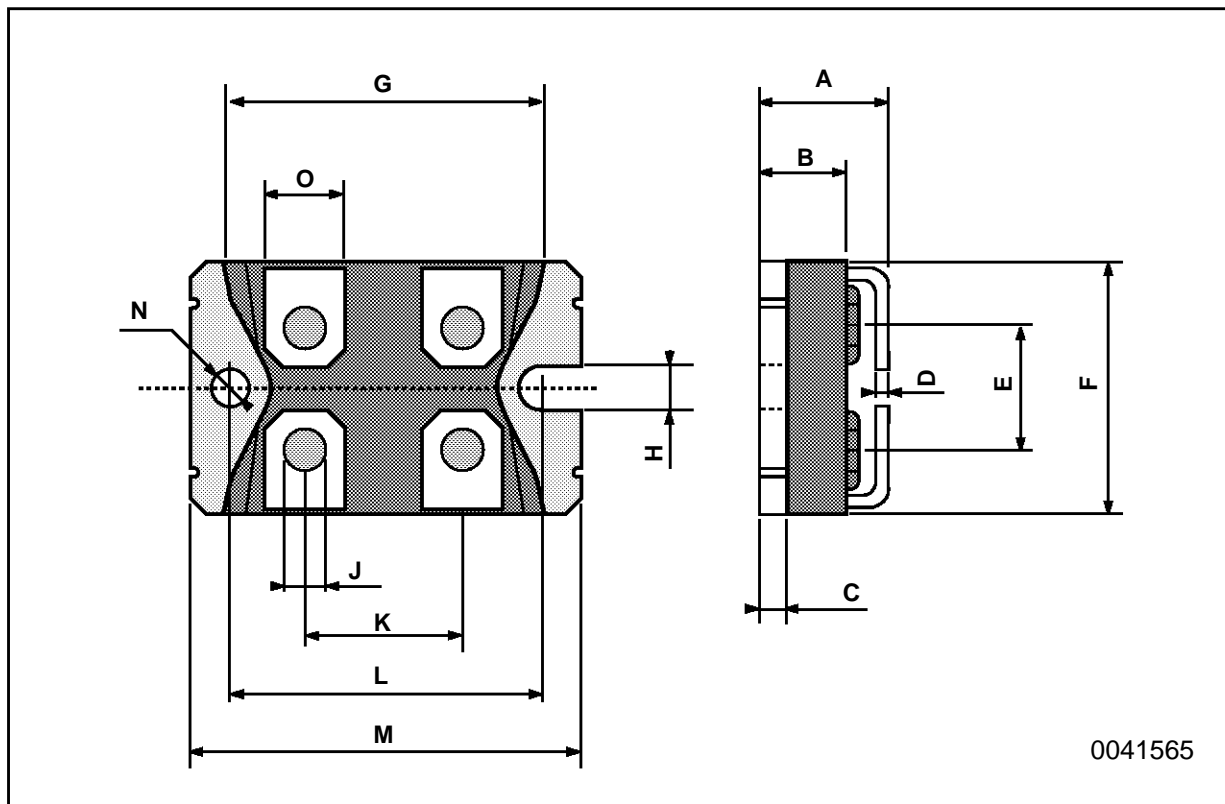


Fig. 3: Test Circuit For Inductive Load Switching And Diode Recovery Times



ISOTOP MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	11.8		12.2	0.466		0.480
B	8.9		9.1	0.350		0.358
C	1.95		2.05	0.076		0.080
D	0.75		0.85	0.029		0.033
E	12.6		12.8	0.496		0.503
F	25.15		25.5	0.990		1.003
G	31.5		31.7	1.240		1.248
H	4			0.157		
J	4.1		4.3	0.161		0.169
K	14.9		15.1	0.586		0.594
L	30.1		30.3	1.185		1.193
M	37.8		38.2	1.488		1.503
N	4			0.157		
O	7.8		8.2	0.307		0.322
P	5.5			0.216		



0041565

Information furnished is believed to be accurate and reliable. However, SGS-THOMSON Microelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of SGS-THOMSON Microelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. SGS-THOMSON Microelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of SGS-THOMSON Microelectronics.

© 1994 SGS-THOMSON Microelectronics - All Rights Reserved

SGS-THOMSON Microelectronics GROUP OF COMPANIES
Australia - Brazil - France - Germany - Hong Kong - Italy - Japan - Korea - Malaysia - Malta - Morocco - The Netherlands -
Singapore - Spain - Sweden - Switzerland - Taiwan - Thailand - United Kingdom - U.S.A